Transistors

4V Drive Pch MOSFET

RSE002P03

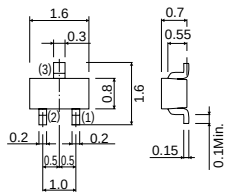
●Structure
Silicon P-channel MOSFET

●Features
1) Low On-resistance.
2) Small package (EMT3).
3) 4V drive.

●Applications
Switching

●Dimensions (Unit : mm)

EMT3



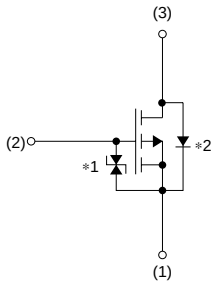
(1)Source
(2)Gate
(3)Drain

Abbreviated symbol : WP

●Package specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSE002P03		○

●Inner circuit



∗1 ESD PROTECTION DIODE
∗2 BODY DIODE

(1) Source
(2) Gate
(3) Drain

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	−30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±0.2	A
	Pulsed	I_{DP} ∗1	±0.4	A
Total power dissipation		P_D ∗2	0.15	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

∗1 Pw≤10μs, Duty cycle≤1%
∗2 Each terminal mounted on a recommended land

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) ∗	833	°C/W

∗ Each terminal mounted on a recommended land

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±10	μA	V_{GS}= ±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	–30	–	–	V	I_D= –1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	–1	μA	V_{DS}= –30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	–1.0	–	–2.5	V	V_{DS}= –10V, I_D= –1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	0.9	1.4	Ω	I_D= –0.2A, V_{GS}= –10V
		–	1.4	2.1	Ω	I_D= –0.15A, V_{GS}= –4.5V
		–	1.6	2.4	Ω	I_D= –0.15A, V_{GS}= –4.0V
Forward transfer admittance	$\|Y_{fs}\|$ *	0.2	–	–	S	V_{DS}= –10V, I_D= –0.15A
Input capacitance	C_{iss}	–	30	–	pF	V_{DS}= –10V
Output capacitance	C_{oss}	–	4	–	pF	V_{GS}= 0V
Reverse transfer capacitance	C_{rss}	–	5	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	8	–	ns	V_{DD}≒ –15V
Rise time	t_r *	–	5	–	ns	I_D= –0.15A
Turn-off delay time	$t_{d\ (off)}$ *	–	30	–	ns	V_{GS}= –10V R_L= 100Ω
Fall time	t_f *	–	40	–	ns	R_G= 10Ω

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	–1.2	V	I_S= –0.1A, V_{GS}=0V

●**Electrical characteristics curves**

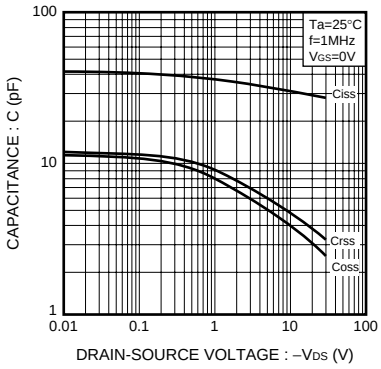


Fig.1 Typical Capacitance vs. Drain-Source Voltage

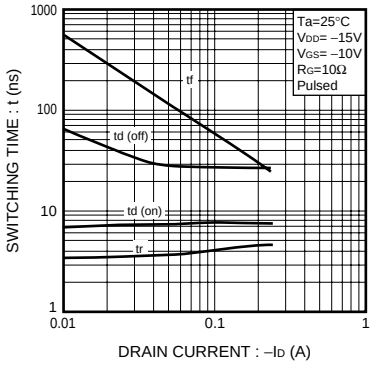


Fig.2 Switching Characteristics

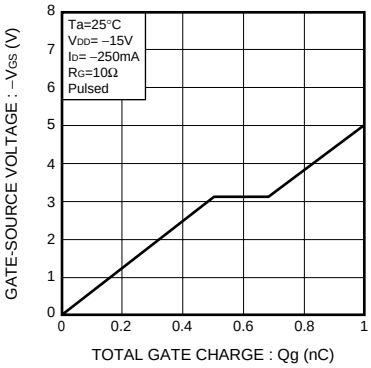


Fig.3 Dynamic Input Characteristics

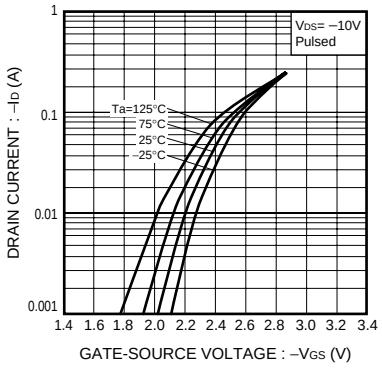


Fig.4 Typical Transfer Characteristics

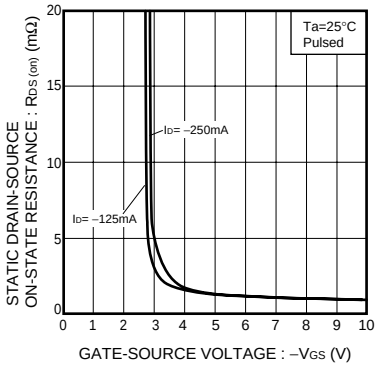


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

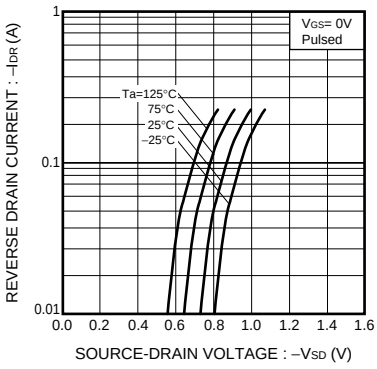


Fig.6 Reverse Drain Current vs. Source-Drain Voltage

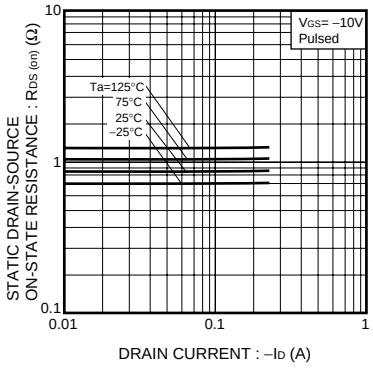


Fig.7 Static Drain-Source On-State Resistance vs. Drain current (I)

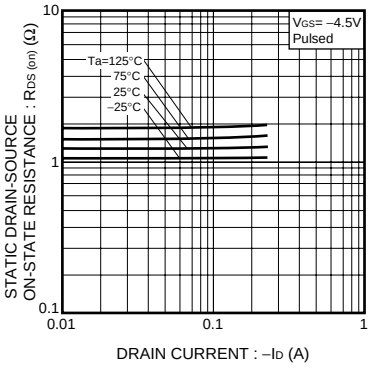


Fig.8 Static Drain-Source On-State Resistance vs. Drain current (II)

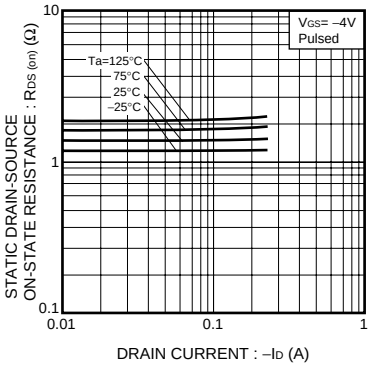


Fig.9 Static Drain-Source On-State Resistance vs. Drain current (III)

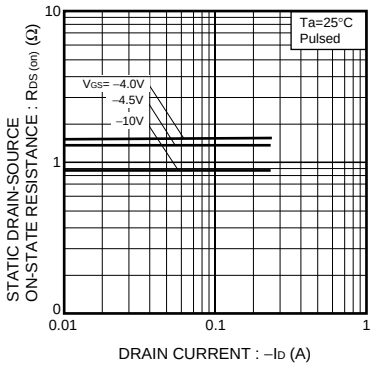


Fig.10 Static Drain-Source On-State Resistance vs. Drain current (Ⅳ)

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